

InGaAsP / InP LED Chip ---TK0912E3A

1. Scope

- The specification applies to light sources in data communication.
- Type : TK0912E3A.

2. Structure

- InGaAsP/InP DH LED Chip.
- P Electrode (anode) : Gold.
- N Electrode (cathode) : Gold.

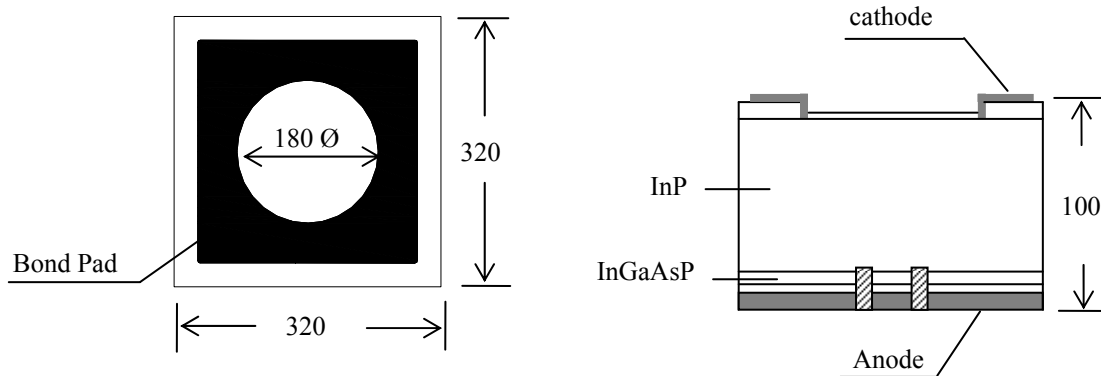
3. Size

- Chip size : $320 \times 320 \pm 25\mu\text{m}$
- Thickness : $100 \pm 25\mu\text{m}$
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

Electro-Optical Specifications @ $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Wavelength	λ	CW	1290	1320	1350	nm
Spectral width	$\Delta\lambda$	CW RMS			170	nm
Chip Power	P_o	$I_f=60\text{mA}$	170			μW
Operating voltage	V_f	CW	1.1	1.2	1.35	V
Leakage current	I_r	$V_r=2\text{V}$			2.00	μA
Bandwidth	Bw	$I_f=60\text{mA}$	155			MHz



Unit : μm

fig. 1

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